

# TXG404x-Q1 4-Bit, ±40V Ground-Level Translator

#### 1 Features

- · Supports DC ground shifts up to ±40V
- AC Noise Rejection up to 130V<sub>PP</sub> at 1MHz and CMTI of 1kV/µs
- Low Prop Delay (8.5ns max) and Ch-Ch Skew (2ns max)
- · 100Mbps data rate
- Low power consumption (0.7mA per channel at 1Mbps, 1.8V)
- Fully configurable dual-rail design allows each port to operate from 1.71V to 5.5V
- 4, 2, 1 channel devices with multiple configurations will be available
- Two device variants:
  - TXG4041: 3 forward, 1 reverse
  - TXG4042: 2 forward, 2 reverse
- Supports V<sub>CC</sub> disconnect feature (I/Os are forced into high-Z)
- Schmitt-trigger inputs allows for slow and noisy signals
- Inputs with integrated static pull-down resistors prevent channels from floating
- Operating temperature from –40°C to +125°C
- Latch-up performance exceeds 100mA per JESD 78. class II
- ESD protection exceeds JESD 22
  - 2000V human-body model
  - 500V charged-device model
- Package option: RUC (X2QFN-14)

## 2 Applications

- Electric Power Steering
- Vehicle Control Unit
- Automotive Display
- Head Unit and Digital Cockpit
- · Test and Measurement
- Factory Automation
- Appliances

#### 3 Description

The TXG404x-Q1 is a 4-bit, fixed direction, non-galvanic based voltage and ground-level translator that can support both logic-level shifting between 1.71V to 5.5V and ground-level shifting up to ±40V. Compared to traditional level shifters, the TXG404x-Q1 family can solve the challenges of voltage translation across different ground levels. The Simplified Block Diagram shows a common use case where there is a DC shift between GNDA to GNDB due to parasitic resistance or capacitance.

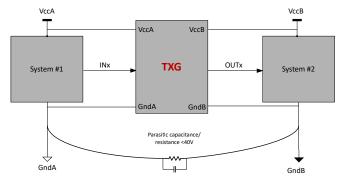
 $V_{CCA}$  is referenced to GNDA and  $V_{CCB}$  is referenced to GNDB. Ax pins are referenced to  $V_{CCA}$  logic levels while Bx pins are referenced to  $V_{CCB}$  logic levels. Both A port and B port can accept voltages from 1.71V to 5.5V. This device includes two enable pins that can place the respective outputs in a high-impedance state when the OE pin is connected to GND or left floating. In the event of input power or signal loss, the output is default low when OE is High (refer to Table 7-1). The max leakage between GNDA and GNDB is  $2\mu A$  when  $V_{CC}$  to GND is shorted.

The TXG404x-Q1 device helps improve noise immunity and power sequencing across different ground domains while providing low power consumption, latency and channel-to-channel skew. It can supress noise levels at 130V<sub>PP</sub> up to 1MHz (Figure 6-1). This device can support multiple interfaces such as SPI, UART, GPIO, and I2S.

#### **Package Information**

		** * * *
PART NUMBER	PACKAGE (1)	BODY SIZE (NOM)
TXG4041-Q1	RUC	2.00mm × 2.00mm
TXG4042-Q1	(X2QFN-14)	2.00111111 ^ 2.00111111

 For all available packages, see the orderable addendum at the end of the data sheet.



**Simplified Block Diagram** 



## **Table of Contents**

1 Features1	7.2 Functional Block Diagram	16
2 Applications 1	7.3 Device Functional Modes	17
B Description1	8 Application and Implementation	18
4 Pin Configuration and Functions3	8.1 Application Information	18
5 Specifications4	8.2 Typical Application	
5.1 Absolute Maximum Ratings4	8.3 Power Supply Recommendations	
5.2 ESD Ratings4	8.4 Layout	20
5.3 Recommended Operating Conditions5	9 Device and Documentation Support	
5.4 Electrical Characteristics6	9.1 Documentation Support	<b>2</b> 1
5.5 Switching Characteristics, V <sub>CCA</sub> = 1.8 ± 0.15 V 9	9.2 Receiving Notification of Documentation Updates.	21
5.6 Switching Characteristics, V <sub>CCA</sub> = 2.5 ± 0.2 V 10	9.3 Support Resources	<b>2</b> 1
5.7 Switching Characteristics, V <sub>CCA</sub> = 3.3 ± 0.3 V 11	9.4 Trademarks	21
5.8 Switching Characteristics, V <sub>CCA</sub> = 5.0 ± 0.5 V 12	9.5 Electrostatic Discharge Caution	<mark>2</mark> 1
5.9 Switching Characteristics: T <sub>sk</sub> , T <sub>MAX</sub> 13	9.6 Glossary	
6 AC Noise Tolerance15	10 Revision History	
7 Detailed Description16	11 Mechanical, Packaging, and Orderable	
7.1 Overview	Information	<b>2</b> 1



## **4 Pin Configuration and Functions**

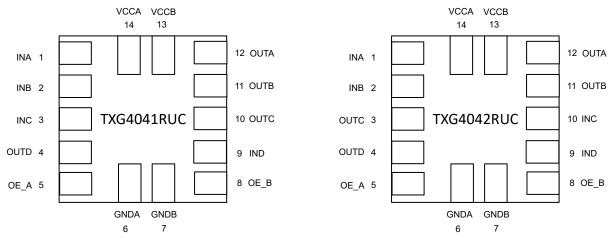


Figure 4-1. TXG4041RUC Package 14-Pin X2QFN Top View

Figure 4-2. TXG4042RUC Package 14-Pin X2QFN Top View

Table 4-1. TXG404x RUC Pin Functions

		iai	DIE 4-1. 17	XG404X RUC PIN Functions
	PIN		1/0	DESCRIPTION
Name	TXG4041	1       I       Input Channel A         2       2       I       Input Channel B         3       10       I       Input Channel C         9       I       Input Channel D         2       12       O       Output Channel A         1       11       O       Output Channel B         0       3       O       Output Channel C         4       4       O       Output Channel D         5       I       Active-High Output Enable (A side). Pull to GND to place all output impedance mode.         8       I       Active-High Output Enable (B side). Pull to GND to place all output impedance mode.         4       14       —       A side supply voltage. 1.71 V ≤ V <sub>CCA</sub> ≤ 5.5 V         3       13       —       B side supply voltage. 1.71 V ≤ V <sub>CCB</sub> ≤ 5.5 V		
INA	1	1	I	Input Channel A
INB	2	2	I	Input Channel B
INC	3	10	I	Input Channel C
IND	9	9	I	Input Channel D
OUTA	12	12	0	Output Channel A
OUTB	11	11	0	Output Channel B
OUTC			0	Output Channel C
OUTD	4	4	0	Output Channel D
OE_A	5	5	I	Active-High Output Enable (A side). Pull to GND to place all outputs in high-impedance mode.
OE_B	8	8	ı	Active-High Output Enable (B side). Pull to GND to place all outputs in high-impedance mode.
V <sub>CCA</sub>	14	14	_	A side supply voltage. 1.71 V ≤ V <sub>CCA</sub> ≤ 5.5 V
V <sub>CCB</sub>	13	13	_	B side supply voltage. 1.71 V ≤ V <sub>CCB</sub> ≤ 5.5 V
GNDA	6	6	_	Ground reference for V <sub>CCA</sub>
GNDB	TXG4041 TXG  NA 1  NB 2  NC 3 1  ND 9  JTA 12 1  JTB 11 1  JTC 10  JTD 4  E_A 5  E_B 8  CCA 14 11  CCB 13 11  NDA 6		_	Ground reference for V <sub>CCB</sub>



## **5 Specifications**

## 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

	anig nee an temperature range (amous cinemise need)		MIN	MAX	UNIT
V <sub>CCA</sub> to V <sub>GNDA</sub>	Supply voltage A to Ground voltage A		-0.5	6.5	V
V <sub>CCB</sub> to V <sub>GNDB</sub>	Supply voltage B to Ground voltage B		-0.5	6.5	V
$V_{GNDA}$ to $V_{GNDB}$	Ground voltage B to Ground voltage A		-42	42	٧
		I/O Ports (A Port) to V <sub>GNDA</sub>	-0.5	6.5	V
VI	Input Voltage <sup>(2)</sup>	I/O Ports (B Port) to V <sub>GNDB</sub>	-0.5	6.5	V
		OE	-0.5	6.5	V
V	Voltage applied to any output in the high-impedance or power-off	A Port to V <sub>GNDA</sub>	-0.5	6.5	V
Vo	state <sup>(2)</sup>	B Port to V <sub>GNDB</sub>	-0.5	6.5	V
V	Valence and indicate any automatic the binds on law state (2) (3)	A Port to V <sub>GNDA</sub>	-0.5	V <sub>CCA</sub> + 0.5	V
Vo	Voltage applied to any output in the high or low state <sup>(2) (3)</sup>	B Port to V <sub>GNDB</sub>	-0.5	V <sub>CCB</sub> + 0.5	V
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < 0	-20		mA
I <sub>OK</sub>	Output clamp current	V <sub>O</sub> < 0	-20		mA
Io	Continuous output current	-	-25	25	mA
	Continuous current through V <sub>CC</sub> or GND		-100	100	mA
Tj	Junction Temperature			150	°C
T <sub>stg</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under <u>Section 5.1</u> may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under <u>Section 5.3</u> Exposure beyond the limits listed in <u>Section 5.3</u> may affect device reliability.

- (2) The input voltage and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
- 3) The output positive-voltage rating may be exceeded up to 6.5V maximum if the output current rating is observed.

### 5.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001	±2500	V
V <sub>(ESD)</sub>	Lieurosiano discriarge	Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002	±500	\ \ \



## **5.3 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted) (1) (2) (3)

			MIN	TYP MAX	UNIT
V <sub>CCA</sub>	Supply voltage A - Relative to GNDA		1.71	5.5	V
V <sub>CCB</sub>	Supply voltage B - Relative to GNDB		1.71	5.5	V
V <sub>GNDA</sub> - V <sub>GNDB</sub>	Voltage Between GNDA and GNDB		-40	40	V
		V <sub>CCO</sub> = 1.71 V	-4.5		
ı	Supply voltage B - Relative to GNDB	V <sub>CCO</sub> = 2.3 V	-8		mA
Іон		V <sub>CCO</sub> = 3 V	-10		IIIA
		V <sub>CCO</sub> = 4.5 V	-12		1
		V <sub>CCO</sub> = 1.71V		4.5	
ı	Low-level output current	V <sub>CCO</sub> = 2.3 V		8	mA
l <sub>OL</sub>	Low-level output current	V <sub>CCO</sub> = 3 V		10	IIIA
		V <sub>CCO</sub> = 4.5 V		12	1
VI	Input voltage - Relative to GNDx	·	0	5.5	V
V <sub>IH</sub>	High-level input voltage		0.7 x V <sub>CCI</sub>		V
V <sub>IL</sub>	High-level output voltage			0.3 x V <sub>CCI</sub>	V
Vo	High-level input voltage High-level output voltage Dutput voltage - Relative to GNDx		0	V <sub>cco</sub>	V
T <sub>A</sub>	Voltage Between GNDA and GNDB  High-level output current  Low-level output current  Input voltage - Relative to GNDx  High-level input voltage  High-level output voltage  Output voltage - Relative to GNDx		-40	125	°C

 $V_{CCI}$  is the  $V_{CC}$  associated with the input port.  $V_{CCO}$  is the  $V_{CC}$  associated with the output port. (1)

<sup>(2)</sup> 

All control inputs and data I/Os of this device have weak pulldowns to ensure the line is not floating when undefined external to the device. The input leakage from these weak pulldowns is defined by the I<sub>I</sub> specification indicated under Section 5.4.



### **5.4 Electrical Characteristics**

over operating free-air temperature range (unless otherwise noted)(1) (2)

						ting free erature (1			
	PARAMETER	TEST CONDITIONS	V <sub>CCA</sub>	V <sub>CCB</sub>	-40°	C to 125°	С	UNIT	
					MIN	TYP	MAX		
		I <sub>OH</sub> = -4.5 mA	1.71 V	1.71 V	1.5				
,	High-level output	I <sub>OH</sub> = -8 mA	2.3 V	2.3 V	2.0			\ /	
/он	voltage (3)	I <sub>OH</sub> = -10 mA	3 V	3 V	2.7			V	
		I <sub>OH</sub> = -12 mA	4.5 V	4.5 V	4.1				
		I <sub>OL</sub> = 4.5 mA	1.71 V	1.71 V			0.16		
,	Low-level output	I <sub>OL</sub> = 8 mA	2.3 V	2.3 V			0.27		
OL.	voltage <sup>(4)</sup>	I <sub>OL</sub> = 10 mA	3 V	3 V			0.34	V	
		I <sub>OL</sub> = 12 mA	4.5 V	4.5 V			0.41		
			1.71 V	1.71 V			1.11		
	Positive-going	Data Inputs	2.3 V	2.3 V			1.40		
/ <sub>T+</sub>	input-threshold	(Ax, Bx)	3 V	3 V			1.73	V	
	voltage	(Referenced to V <sub>CCI</sub> )	4.5 V	4.5 V			2.45		
			5.5 V	5.5 V			3.0		
			1.71 V	1.71 V			1.10		
	Positive-going		2.3 V	2.3 V			1.40		
/ <sub>T+</sub>	input-threshold	OE (Referenced to V <sub>CCA</sub> or V <sub>CCB)</sub>	3 V	3 V			1.72	V	
	voltage	(Lyeleleliced to ACCM of ACCB)	4.5 V	4.5 V		,	2.45		
			5.5 V	5.5 V		,	2.96		
			1.71 V	1.71 V	0.56				
	Negative-going	Data Inputs	2.3 V	2.3 V	0.80			V	
/ <sub>T-</sub>	input-threshold	(Ax, Bx)	3 V	3 V	1.15				
	voltage	(Referenced to V <sub>CCI</sub> )	4.5 V	4.5 V	1.61				
			5.5 V	5.5 V	2.0				
			1.71 V	1.71 V	0.5		0.72		
	Negative-going		2.3 V	2.3 V	0.80		0.87		
/ <sub>T-</sub>	input-threshold	OE (Referenced to V <sub>CCA</sub> or V <sub>CCB</sub> )	3 V	3 V	1.1		1.23	V	
	voltage	(Keleleliced to ACCV of ACCB)	4.5 V	4.5 V	1.7		1.96		
			5.5 V	5.5 V	2.2		2.43		
			1.71 V	1.71 V	0.3		0.50		
	Input-threshold	Data Inputs	2.3 V	2.3 V	0.36		0.60		
ΔV <sub>T</sub>	hysteresis	(Ax, Bx)	3 V	3 V	0.38		0.54	V	
	$(V_{T+}-V_{T-})$	(Referenced to V <sub>CCI</sub> )	4.5 V	4.5 V	0.41		0.82		
			5.5 V	5.5 V	0.40		0.96		
			1.71 V	1.71 V	0.29		0.45		
	Input-threshold		2.3 V	2.3 V	0.35		0.58		
ΔV <sub>T</sub>	hysteresis	OE (Peferenced to V or V	2)/ 2)/ 0.20			-	0.54	V	
	$(V_{T+}-V_{T-})$	(Referenced to V <sub>CCA</sub> or V <sub>CCB)</sub>	4.5 V	4.5 V	0.41		0.58		
			5.5 V	5.5 V	0.43		0.62		
ı	Input leakage current	Data Inputs (Ax, Bx) V <sub>I</sub> = V <sub>CCI</sub> or GND	1.71V – 5.5V	1.71V – 5.5V	0.2		1.6	μА	



over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup> (2)

·		rature range (unless otherw	,			ting free-air erature (T <sub>A</sub> )	
P	ARAMETER	TEST CONDITIONS	V <sub>CCA</sub>	V <sub>CCB</sub>	-40°	C to 125°C	UNIT
					MIN	TYP MAX	
	Partial power down	A Port or B Port	0 V	0 V - 5.5 V	-5	5	μΑ
I <sub>off</sub>	current	V <sub>I</sub> = 1.71 V - 5.5 V	0 V - 5.5 V	0 V	-5	5	μΑ
_	Floating supply	A Port or B Port	Floating <sup>(5)</sup>	0 V - 5.5 V	-2.5	2.5	
off-float	Partial power down current	V <sub>I</sub> = GND	0 V - 5.5 V	Floating <sup>(5)</sup>	-2.5	2.5	μA
I <sub>O</sub>	Tri-state output Output current	A or B Port: $V_I = V_{CCA}$ or $V_{GNDA}$ OE = GND	1.71V – 5.5V	1.1V – 5.5V	-5	5	μА
C <sub>i</sub>	Control Input Capacitance	V <sub>I</sub> = 3.3 V or V <sub>GNDA</sub>	3.3 V	3.3 V	1	2	pF
C <sub>io</sub>	Data I/O Capacitance	OE = GND, V <sub>O</sub> = 1.71V DC +1 MHz -16 dBm sine wave	3.3 V	3.3 V	1	3	pF
$C_{GND}$	Cap between grounds	All channels combined (V <sub>CC</sub> both sides are powered on)				46	pF
$C_{GND}$	Cap between grounds	All channels combined (V <sub>CC</sub> to GND shorted)				53	pF
Leakage	Current Leakage between GndA to GndB	All channels combined (V <sub>CC</sub> both sides are powered on and inputs are all low)	1.71V – 5.5V	1.71V – 5.5V		2	μА
Leakage	Current Leakage between GndA to GndB	All channels combined (V <sub>CC</sub> both sides are powered on and inputs are all high)	1.71V – 5.5V	1.71V – 5.5V		44	μА
Leakage	Current Leakage between GndA to GndB	All channels combined (V <sub>CC</sub> to GND shorted)	1.71V – 5.5V	1.71V – 5.5V		2	μΑ
CMTI	Common Mode Transient Immunity	Input toggling at 100Mbps Ground shift up to 40V	1.71V – 5.5V	1.71V – 5.5V		1	kV/µs
		V V 0VD	1.71V – 5.5V	1.71V – 5.5V	546	1220	
		$V_1 = V_{CCI}$ or GND $I_0 = 0$	0 V	5.5 V	-3	13	
$I_{CCA}$	V <sub>CCA</sub> supply current		5.5 V	0 V	509	1050	μΑ
		V <sub>I</sub> = GND I <sub>O</sub> = 0	5.5 V	Floating <sup>(5)</sup>	509	1050	
		., .,	1.71V – 5.5V	1.71V – 5.5V	760	1836	
		$V_1 = V_{CCI}$ or GND $I_0 = 0$	0 V	5.5 V	654	1350	
I <sub>CCB</sub>	V <sub>CCB</sub> supply current		5.5 V	0 V	-3	36	μA
	Common Mode Transient Immunity Input toggling at 100Mbl Ground shift up to 40V $V_{CCA} \text{ supply current} \qquad V_I = V_{CCI} \text{ or GND} \\ I_O = 0 \\ V_I = GND \\ I_O = 0 \\ V_I = V_{CCI} \text{ or GND} \\ $		Floating <sup>(5)</sup>	5.5 V	656	1350	
			1.8V	1.8V	1.9	3.1	
I <sub>CCA</sub> +	Supply Current -	EN - 0	2.5V	2.5V	1.9	3.1	m ^
I <sub>CCB</sub>	Disable	EN = 0	3.3V	3.3V	2.0	3.1	- mA
			5V	5V	2.1	3.3	



over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup> (2)

P	ARAMETER	TEST CONDITIONS	V <sub>CCA</sub>	V <sub>CCB</sub>	tempe	ting free-air erature (T <sub>A</sub> ) C to 125°C	UNIT
					MIN	TYP MAX	(
			1.8V	1.8V	1	2.6	5
		\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	2.5V	2.5V	1.3	2.	
		$V_I = V_{CCI}$	3.3V	3.3V	1.3	2.8	mA
I <sub>CCA</sub> +	Supply Current -		5V	5V	1.4	3.	ı
I <sub>CCB</sub>	DC Signal		1.8V	1.8V	1.2	2.	7
		V OND	2.5V	2.5V	1.3	2.	
		V <sub>I</sub> = GND	3.3V	3.3V	1.3	2.8	mA
			5V	5V	1.4	3.	1
			1.8V	1.8V	1.5	2.0	3
		All channels switching with	2.5V	2.5V	1.6	2.	7
		square wave clock input; CL = 15 pF, 1Mbps	3.3V	3.3V	1.6	2.8	mA
I <sub>CCA</sub> +			5V	5V	1.9	3.5	3
			1.8V	1.8V	9.2	12.	1
	Supply Current - AC	All channels switching with square wave clock input; CL	2.5V	2.5V	10.8	14	ı mA
I <sub>CCB</sub>	Signal	= 15 pF, 50Mbps	3.3V	3.3V	12.4	16.2	2 111/4
			5V	5V	17.6	20.0	3
			1.8V	1.8V	16.5	20.	
		All channels switching with square wave clock input; CL	2.5V	2.5V	20.2	24.	mA
		= 15 pF, 100Mbps	3.3V	3.3V	24.1	29	9 1114
			5V	5V	35	38	3
	Positive-Going	A Supply	1.71V – 5.5V			1548	
$V_{UVLO+}$	Undervoltage Lockout Voltage	B Supply		1.71V – 5.5V		1548	mV
.,	Lockout Voltage  Negative-Going	A Supply	1.71V – 5.5V		1492		.,
V <sub>UVLO-</sub>	Undervoltage Lockout Voltage	B Supply		1.71V – 5.5V	1492		mV
V	Undervoltage	A Supply	1.71V – 5.5V		35	132	2 mV
$V_{\text{UVLO\_Hys}}$	Lockout Hysteresis	B Supply		1.71V – 5.5V	35	132	2 1110

- $V_{\text{CCI}}$  is the  $V_{\text{CC}}$  associated with the input port and referenced to  $\text{GND}_{\text{A}}$
- $V_{CCO}$  is the  $V_{CC}$  associated with the output port and referenced to  $\mbox{GND}_{\mbox{\footnotesize B}}$
- (1) (2) (3) (4)
- Tested at  $V_I = V_{T+(MAX)}$ Tested at  $V_I = V_{T-(MIN)}$ Floating is defined as a node that is both not actively driven by an external device and has leakage not exceeding 10nA



# 5.5 Switching Characteristics, $V_{CCA} = 1.8 \pm 0.15 V$

								I	B-Port Supply	Voltage	(V <sub>CCB</sub> )					
ı	PARAMETER	TEST CONDITIONS	FROM	то	TEMPERATURE	1.8	± 0.15 V	2.	5 ± 0.2 V	3.3	3 ± 0.3 V	5.0	0 ± 0.5 V	UNIT		
						MIN	TYP MAX	MIN	TYP MAX	MIN	TYP MAX	MIN	TYP MAX			
			А	В	-40°C to 85°C	3	7.4	3	7.5	3.1	7.5	3.1	7.9			
	Dranagation dalay	1Mbps all 4 channels	Α	В	-40°C to 125°C	3	7.8	3	7.8	3.1	7.9	3.1	8.4			
t <sub>pd</sub>	Propagation delay	toggling	В	Α	-40°C to 85°C	3	7.4	2.8	5.8	2.8	5.2	2.8	4.9	ns		
			В	Α	-40°C to 125°C	3	7.8	2.8	6.1	2.8	5.5	2.8	5.2			
			OE	Α	-40°C to 85°C	17.6	40.9	12.6	28.2	14.7	27.4	10	18.8			
	Disable time		OE	Α	-40°C to 125°C	17.6	42	12.6	29.1	14.7	28	10	19.3			
t <sub>dis</sub>	Disable time		OE	В	-40°C to 85°C	16.1	35	16.1	35	16.1	35	16.1	35	ns		
			OE	В	-40°C to 125°C	16.1	35.6	16.1	35.5	16.1	35.6	16.1	35.6			
			OE	Α	-40°C to 85°C	7.5	26.5	5.5	15.3	4.5	11	3.8	7.9			
	Fu abla tima		OE	Α	-40°C to 125°C	7.9	27.5	5.5	16.3	4.5	11.8	3.8	8.4			
t <sub>en</sub>	Enable time		OE	В	-40°C to 85°C	5.4	18.1	5.4	18.1	5.4	18.1	5.4	18.1	ns		
			OE	В	-40°C to 125°C	5.4	18.9	5.4	18.8	5.4	18.9	5.4	18.8			
	Pulse width distortion		Α	В	-40°C to 85°C		1.6	,	1.5		1.4		1.3			
DIA/ID			Itobi - tolbi	Itohi - tohi	Α	В	-40°C to 125°C		1.6	,	1.5		1.4		1.3	
PWD			В	Α	-40°C to 85°C		1.6		1.5		1.4		1.3	ns		
			В	Α	-40°C to 125°C		1.6		1.5		1.4		1.4			
			Α	В	-40°C to 85°C		1.1		1.2		1.5		1.8			
	Output signal rise		Α	В	-40°C to 125°C	0.6	1.3	0.5	1.5	0.5	1.6	0.6	1.9			
r	time		В	Α	-40°C to 85°C	0.5	0.9	0.5	1	0.5	0.9	0.5	0.9	ns		
			В	Α	-40°C to 125°C	0.5	1	0.5	1.1	0.5	1	0.5	1.1			
			Α	В	-40°C to 85°C	0.5	1.3	0.5	1.6	0.5	1.6	0.6	1.9			
f	Output signal fall		Α	В	-40°C to 125°C	0.5	1.6	0.5	1.8	0.5	1.9	0.6	2.2	1		
ī	time		В	Α	-40°C to 85°C	0.5	1.1	0.5	1.1	0.5	1.1	0.5	1.1	ns		
			В	Α	-40°C to 125°C	0.5	1.4	0.5	1.5	0.5	1.4	0.5	1.4			
	Default output	Measured from the			-40°C to 85°C	4.2	7.7	4.1	7.6	4.1	7.5	3.9	7.4			
DO	delay time from input power loss	time V <sub>CC</sub> goes below 1.49V			-40°C to 125°C	4.2	7.7	4.1	7.6	4.1	7.5	3.9	7.4	μs		
	Time from ULVO				-40°C to 85°C	21.2	54.2	21.2	54.1	21.2	54.1	21.2	54.1			
PU	to valid output data				-40°C to 125°C	20.8	54.2	20.8	54.1	20.8	54.1	20.8	54.1	μs		



# 5.6 Switching Characteristics, $V_{CCA}$ = 2.5 ± 0.2 V

		, 00						[	B-Port Supply \	/oltage	(V <sub>CCB</sub> )				
F	PARAMETER	TEST CONDITIONS	FROM	то	TEMPERATURE	1.8	± 0.15 V	2.	5 ± 0.2 V	3.	3 ± 0.3 \	/	5.0	) ± 0.5 V	UNIT
						MIN	TYP MAX	MIN	TYP MAX	MIN	TYP	MAX	MIN	TYP MAX	
			А	В	-40°C to 85°C	2.9	5.9	2.9	5.9	2.9		6	3	6.2	2
	Dranagation dalay	1Mbps all 4 channels	Α	В	-40°C to 125°C	2.9	6.1	2.9	6.2	2.9		6.3	3	6.6	
t <sub>pd</sub>	Propagation delay	toggling	В	Α	-40°C to 85°C	3	7.4	2.9	5.9	2.8		5.2	2.8	5	ns
			В	Α	-40°C to 125°C	3	7.8	2.9	6.2	2.8		5.6	2.8	5.4	ļ.
			OE	Α	-40°C to 85°C	17.6	40.9	12.6	28.3	14.7		27.4	10.1	18.8	3
	Diaghta times		OE	Α	-40°C to 125°C	17.6	41.9	12.6	29.1	14.7		28	10.1	19.3	
t <sub>dis</sub>	Disable time		OE	В	-40°C to 85°C	11.6	24.7	11.6	24.7	11.6		24.7	11.6	24.7	ns
			OE	В	-40°C to 125°C	11.6	25.2	11.6	25.2	11.6		25.2	11.6	25.2	2
			OE	Α	-40°C to 85°C	7.5	26.5	5.5	15.3	4.5		11	3.8	7.8	3
	Enable time		OE	Α	-40°C to 125°C	7.9	27.5	5.5	16.3	4.5		11.8	3.8	8.4	
t <sub>en</sub>			OE	В	-40°C to 85°C	3.8	10.9	3.8	10.9	3.8		10.9	3.8	10.9	ns )
			OE	В	-40°C to 125°C	3.8	11.6	3.8	11.6	3.8		11.6	3.8	11.6	5
			Α	В	-40°C to 85°C		0.9		0.8			0.8		0.7	,
חאים	Pulse width distortion	t <sub>phi</sub> - t <sub>plh</sub>	Α	В	-40°C to 125°C		0.9		0.8			8.0		0.7	
PWD		T <sub>phi</sub> - T <sub>pih</sub>	В	Α	-40°C to 85°C		0.9		0.8			8.0		0.7	ns
			В	Α	-40°C to 125°C		0.9		0.8			0.8		0.7	,
			Α	В	-40°C to 85°C	0.6	1.1	0.5	1.2	0.5		1.5	0.6	1.8	3
	Output signal rise		Α	В	-40°C to 125°C	0.6	1.3	0.5	1.4	0.5		1.7	0.6	1.9	
t <sub>r</sub>	time		В	Α	-40°C to 85°C	0.5	1	0.5	1	0.5		1	0.5	1	ns
			В	Α	-40°C to 125°C	0.5	1.1	0.5	1.2	0.5		1.2	0.5	1.1	
			Α	В	-40°C to 85°C	0.5	1.2	0.5	1.5	0.5		1.7	0.5	1.9	)
tf	Output signal fall		Α	В	-40°C to 125°C	0.5	1.6	0.5	1.7	0.5		1.8	0.5	2.1	
u	time		В	Α	-40°C to 85°C	0.5	1.3	0.5	1.3	0.5		1.4	0.5	1.3	ns B
			В	Α	-40°C to 125°C	0.5	1.5	0.5	1.5	0.5		1.5	0.5	1.6	5
	Default output	Measured from the			-40°C to 85°C	4.2	7.7	4.1	7.6	4.1		7.5	3.9	7.4	
t <sub>DO</sub>	delay time from input power loss	time V <sub>CC</sub> goes below 1.49V)			-40°C to 125°C	4.2	7.7	4.1	7.6	4.1		7.5	3.9	7.4	μs
	Time from ULVO				-40°C to 85°C	26	61	26	61.1	26		61	26	61	
t <sub>PU</sub>	to valid output data				-40°C to 125°C	25.6	61	25.6	61.1	25.6		61	25.6	61	μs



# 5.7 Switching Characteristics, $V_{CCA}$ = 3.3 ± 0.3 V

								I	B-Port Supply	Voltage	(V <sub>CCB</sub> )				
ı	PARAMETER	TEST CONDITIONS	FROM	то	TEMPERATURE	1.8	± 0.15 V	2.	5 ± 0.2 V	3.3	3 ± 0.3 V	5.0	0 ± 0.5 V	UNIT	
						MIN	TYP MAX	MIN	TYP MAX	MIN	TYP MAX	MIN	TYP MAX	1	
			Α	В	-40°C to 85°C	2.9	5.2	2.9	5.3	2.8	5.4	3	5.7		
	Propagation delay	1Mbps all 4 channels	Α	В	-40°C to 125°C	2.9	5.5	2.9	5.6	2.8	5.8	3	6.1	ns	
t <sub>pd</sub>	Propagation delay	toggling	В	Α	-40°C to 85°C	3	7.5	2.9	5.9	2.8	5.3	2.8	5.1	1115	
			В	Α	-40°C to 125°C	3	7.9	2.9	6.3	2.8	5.7	2.8	5.5	1	
			OE	Α	-40°C to 85°C	17.6	40.9	12.6	28.2	14.7	27.4	10.1	18.8		
	Disable time		OE	Α	-40°C to 125°C	17.6	41.9	12.6	29	14.7	28	10.1	19.3		
t <sub>dis</sub>	Disable time		OE	В	-40°C to 85°C	13.9	25.3	13.8	25.3	13.8	25.3	13.8	25.3	ns	
			OE	В	-40°C to 125°C	13.9	25.7	13.8	25.7	13.8	25.7	13.8	25.7	1	
			OE	Α	-40°C to 85°C	7.5	26.5	5.5	15.3	4.5	11	3.8	7.8		
	En abla fina		OE	Α	-40°C to 125°C	8	27.5	5.5	16.3	4.5	11.8	3.8	8.4		
t <sub>en</sub>	Enable time		OE	В	-40°C to 85°C	3	8	3.1	8	3.1	8	3	8	ns	
			OE	В	-40°C to 125°C	3	8.5	3.1	8.5	3.1	8.6	3	8.5		
	Pulse width distortion		А	В	-40°C to 85°C		0.7	,	0.6		0.5		0.5		
DIAID		t <sub>phi</sub> - t <sub>pih</sub>	Itabi - taibi	Α	В	-40°C to 125°C		0.7		0.6		0.5		0.5	
PWD			В	Α	-40°C to 85°C		0.7		0.6		0.5		0.5	ns	
			В	Α	-40°C to 125°C		0.7		0.6		0.5		0.5	1	
			Α	В	-40°C to 85°C	0.6	1.1	0.6	1.2	0.5	1.5	0.6	1.8		
	output signal rise		Α	В	-40°C to 125°C	0.6	1.3	0.6	1.5	0.5	1.7	0.6	1.9		
r	time		В	Α	-40°C to 85°C	0.6	1.1	0.6	1.2	0.5	1.5	0.6	1.8	ns	
			В	Α	-40°C to 125°C	0.6	1.3	0.6	1.5	0.5	1.7	0.6	1.9	1	
			А	В	-40°C to 85°C	0.5	1.2	0.5	1.6	0.5	1.6	0.6	1.9		
ı.e	output signal fall		Α	В	-40°C to 125°C	0.5	1.7	0.5	1.7	0.5	1.8	0.6	2.1	1	
tf	time		В	Α	-40°C to 85°C	0.5	1.4	0.5	1.5	0.5	1.4	0.5	1.5	ns	
			В	Α	-40°C to 125°C	0.5	1.7	0.5	1.7	0.5	1.7	0.5	1.6		
	Default output	Measured from the			-40°C to 85°C	4.2	7.7	4.1	7.6	4.1	7.5	3.9	7.4		
t <sub>DO</sub>	delay time from input power loss	time V <sub>CC</sub> goes below 1.49V			-40°C to 125°C	4.2	7.7	4.1	7.6	4.1	7.5	3.9	7.4	μs	
	Time from ULVO				-40°C to 85°C	26	61	26	61.1	26	61	26	61		
t <sub>PU</sub>	to valid output data				-40°C to 125°C	25.6	61	25.6	61.1	25.6	61	25.6	61	μs	



# 5.8 Switching Characteristics, $V_{CCA}$ = 5.0 ± 0.5 V

									<b>B-Port Supply</b>	Voltage	(V <sub>CCB</sub> )			
P	ARAMETER	TEST CONDITIONS	FRO M	то	TEMPERATURE	1.8	8 ± 0.15 V	2	.5 ± 0.2 V	3	.3 ± 0.3 V	5	.0 ± 0.5 V	UNIT
			141			MIN	TYP MAX	MIN	TYP MAX	MIN	TYP MAX	MIN	TYP MAX	
			Α	В	-40°C to 85°C	2.8	5	2.8	5	2.9	5.2	2.9	5.5	
	Propagation	1Mbps all 4 channels	Α	В	-40°C to 125°C	2.8	5.3	2.8	5.3	2.9	5.6	2.9	5.9	
	delay	toggling	В	Α	-40°C to 85°C	3.1	7.8	3	6.3	2.9	5.7	2.8	5.6	ns
			В	Α	-40°C to 125°C	3.1	8.3	3	6.6	2.9	6.1	2.8	5.8	
			OE	Α	-40°C to 85°C	17.7	40.9	12.6	28.3	14.7	27.4	10.1	18.8	
	Disable time		OE	Α	-40°C to 125°C	17.7	41.9	12.6	29.1	14.7	28	10.1	19.4	
t <sub>dis</sub>	Disable time		OE	В	-40°C to 85°C	9.4	17.4	9.4	17.4	9.4	17.4	9.4	17.4	ns
			OE	В	-40°C to 125°C	9.4	17.7	9.4	17.7	9.4	17.7	9.4	17.7	
t <sub>en</sub> Enable time			OE	Α	-40°C to 85°C	7.5	26.5	5.5	15.3	4.5	11	3.8	7.8	
	Fundale times		OE	Α	-40°C to 125°C	8	27.5	5.5	16.3	4.5	11.8	3.8	8.4	
	Enable time		OE	В	-40°C to 85°C	2.5	5.9	2.5	5.9	2.5	5.9	2.5	5.9	ns
			OE	В	-40°C to 125°C	2.5	6.3	2.5	6.3	2.5	6.3	2.5	6.3	
55	Pulse width distortion		Α	В	-40°C to 85°C		0.5		0.4		0.3		0.3	
		t <sub>phi</sub> - t <sub>plh</sub>	Α	В	-40°C to 125°C		0.5		0.4		0.3		0.3	
PWD			В	Α	-40°C to 85°C		0.5		0.4		0.3		0.3	ns
			В	Α	-40°C to 125°C		0.5		0.4		0.3		0.3	
			Α	В	-40°C to 85°C	0.6	1.1	0.5	1.1	0.5	1.6	0.6	1.8	
	Output signal		Α	В	-40°C to 125°C	0.6	1.3	0.5	1.5	0.5	1.7	0.6	1.9	
r	rise time		В	Α	-40°C to 85°C	0.5	1.6	0.5	1.6	0.5	1.7	0.5	1.7	ns
			В	Α	-40°C to 125°C	0.5	1.7	0.5	1.7	0.5	1.8	0.5	1.7	
			Α	В	-40°C to 85°C	0.5	1.4	0.4	1.6	0.5	1.8	0.6	1.9	
f	Output signal fall		Α	В	-40°C to 125°C	0.5	1.7	0.5	1.7	0.5	1.8	0.6	2.2	
u	time		В	Α	-40°C to 85°C	0.5	1.4	0.5	1.6	0.5	1.8	0.6	1.9	ns
			В	Α	-40°C to 125°C	0.5	1.7	0.5	1.7	0.5	1.8	0.6	2.2	
	Default output	Measured from the			-40°C to 85°C	4.2	7.7	4.1	7.6	4.1	7.5	3.9	7.4	
DO	delay time from input power loss	time V <sub>CC</sub> goes below 1.49V			-40°C to 125°C	4.2	7.7	4.1	7.6	4.1	7.5	3.9	7.4	μs
t <sub>au</sub>	Time from ULVO to valid output				-40°C to 85°C	43.7	96.6	43.7	96.6	43.7	96.6	43.7	96.6	μs
PU	data				-40°C to 125°C	43.7	96.6	43.7	96.6	43.7	96.6	43.7	96.6	μS



## 5.9 Switching Characteristics: T<sub>sk</sub>, T<sub>MAX</sub>

over operating free-air temperature range (unless otherwise noted)

						Operating free-air temperature (T <sub>A</sub> )					
	PARAME	TER	TEST CONI	DITIONS	V <sub>CCI</sub>	V <sub>cco</sub>	-40°C to 125°C			UNIT	
							MIN	TYP	MAX		
				1.65 V - 1.95 V	1.65 V - 1.95 V	100			Mbps		
			50% Duty Cycle Input One channel switching 20% of pulse > 0.7*V <sub>CCO</sub> 20% of pulse < 0.3*V <sub>CCO</sub>	No Translation	2.3 V - 2.7 V	2.3 V - 2.7 V	100			Mbps	
					3.0 V - 3.6 V	3.0 V - 3.6 V	100			Mbps	
					4.5 V - 5.5 V	4.5 V - 5.5 V	100			Mbps	
				Up Translation	1.65 V - 1.95 V	2.3 V - 2.7 V	100			Mbps	
					1.65 V - 1.95 V	3.0 V - 3.6 V	100			Mbps	
		Maximum Data Rate			1.65 V - 1.95 V	4.5 V - 5.5 V	100	-		Mbps	
_					2.3 V - 2.7 V	3.0 V - 3.6 V	100			Mbps	
T <sub>MAX</sub>					2.3 V - 2.7 V	4.5 V - 5.5 V	100			Mbps	
					3.0 V - 3.6 V	4.5 V - 5.5 V	100			Mbps	
					2.3 V - 2.7 V	1.65 V - 1.95 V	100			Mbps	
					3.0 V - 3.6 V	2.3 V - 2.7 V	100	-		Mbps	
			Down Translation	3.0 V - 3.6 V	1.65 V - 1.95 V	100			Mbps		
				4.5 V - 5.5 V	3.0 V - 3.6 V	100			Mbps		
					4.5 V - 5.5 V	2.3 V - 2.7 V	100			Mbps	
				4.5 V - 5.5 V	1.65 V - 1.95 V	100			Mbps		

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONE	DITIONS	V <sub>cci</sub>	V <sub>cco</sub>	Operating free-air temperature (T <sub>A</sub> )			UNIT
		TEOT COME	• CCI	₹660	-40°C to 125°C			Oitii	
						MIN	TYP	MAX	
			No Translation	1.65 V - 1.95 V	1.65 V - 1.95 V			2	ns
		Timing skew between any switching outputs on the rising or falling edge (same direction channels)		2.3 V - 2.7 V	2.3 V - 2.7 V			2	ns
				3.0 V - 3.6 V	3.0 V - 3.6 V			2	ns
				4.5 V - 5.5 V	4.5 V - 5.5 V			2	ns
			Up Translation	1.65 V - 1.95 V	2.3 V - 2.7 V			2	ns
				1.65 V - 1.95 V	3.0 V - 3.6 V			2	ns
	Output skew			1.65 V - 1.95 V	4.5 V - 5.5 V		,	2	ns
t <sub>sk</sub>				2.3 V - 2.7 V	3.0 V - 3.6 V			2	ns
				2.3 V - 2.7 V	4.5 V - 5.5 V			2	ns
				3.0 V - 3.6 V	4.5 V - 5.5 V			2	ns
			Down Translation	2.3 V - 2.7 V	1.65 V - 1.95 V			2	ns
				3.0 V - 3.6 V	2.3 V - 2.7 V			2	ns
				3.0 V - 3.6 V	1.65 V - 1.95 V			2	ns
				4.5 V - 5.5 V	3.0 V - 3.6 V			2	ns
				4.5 V - 5.5 V	2.3 V - 2.7 V		,	2	ns
				4.5 V - 5.5 V	1.65 V - 1.95 V			2	ns



### **6 AC Noise Tolerance**

TXG404x supports I/O voltage translation in environments with noisy grounds. The plot below illustrates the amount of noise that TXG404x can reject in terms of peak-to-peak voltage over frequency.

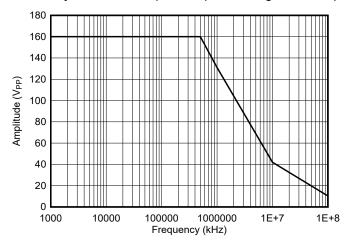


Figure 6-1. AC Noise Rejection Plot



## 7 Detailed Description

#### 7.1 Overview

The TXG404x-Q1 is a 4-bit translating transceiver that uses two individually configurable power-supply rails. The device is operational with  $V_{CCA}$  and  $V_{CCB}$  supplies as low as 1.71V and as high as 5.5V. The A port is designed to track  $V_{CCA}$ , and the B port is designed to track  $V_{CCB}$ . In addition to I/O level shifting, the device supports ground mismatch between two systems up to +/-40V.

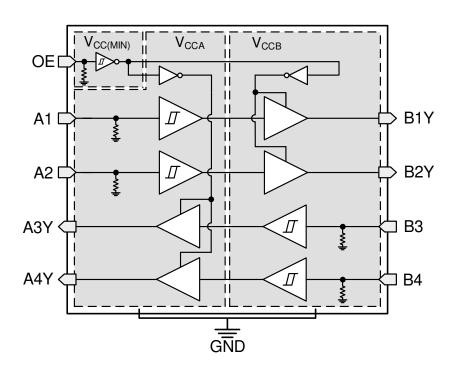
The TXG404x-Q1 device is designed for asynchronous communication between data buses, and transmits data with fixed direction from the A bus to the B bus on some channels and from the B bus to the A bus on the remaining channels. The output-enable input (OE) is used to disable the outputs so the buses are effectively isolated. The output-enable pin (OE) can be referenced to either  $V_{CCA}$  or  $V_{CCB}$ . The OE pin can be left floating or externally pulled down to ground to keep the level shifter outputs in a high-impedance state during power-up or power-down.

This device is fully specified for partial-power-down applications using the  $I_{off}$  current. The  $I_{off}$  protection circuitry ensures that no excessive current is drawn from or sourced into an input or output while the device is powered down.

The  $V_{CC}$  disconnect feature ensures that if  $V_{CC}$  is disconnected with the complementary supply within recommended operating conditions, outputs are disabled and set to the high-impedance state while the supply current is maintained. The  $I_{off-float}$  circuitry ensures that no excessive current is drawn from or sourced into an input or output while the supply is floating.

Glitch-free power supply sequencing allows either supply rail to be powered on or off in any order while providing robust power sequencing performance.

#### 7.2 Functional Block Diagram





### 7.3 Device Functional Modes

**Table 7-1. Function Table** 

Power Supply (	1)	Control Inputs	Port Status				
VCCI	vcco	OE	Input	Output			
PU	PU	Н	Н	Н			
PU	PU	Н	L	L			
PU	PU	L or Open	Х	Hi-Z			
PU	PU	Н	Open	L			
PD	PU	Н	X	L			
Х	PU	L or Open	X	High-Z			
Х	PU	Н	Х	L			
Х	PD	X	X	Undetermined			

<sup>(1)</sup> In the table above: PU = Powered Up; PD = Powered Down; X = Irrelevant; H = High Level; L = Low Level; Open = Floating



## 8 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

## 8.1 Application Information

The TXG404x-Q1 device is used for level translation, enabling communication between devices or systems operating at different interface voltages and ground voltages. Figure 8-1 is an example of two systems that translate from 3.3V to 1.8V across an SPI interface while also experiencing a ground shift of 5V. The ground shift occurs due to the parasitic resistance of the cable used to connect the 48V battery ground and 12V battery ground to the chassis of the car. The TXG404x-Q1 device is ideal for use in applications where a push-pull driver is connected to the data inputs.

#### 8.2 Typical Application

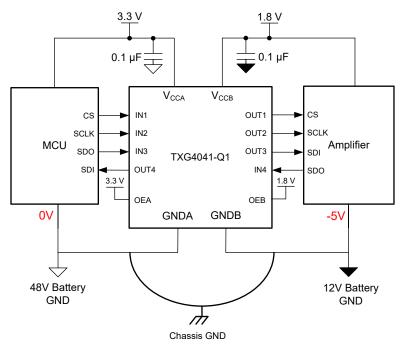


Figure 8-1. TXG404x SPI Interface Application in Automotive

#### 8.2.1 Design Requirements

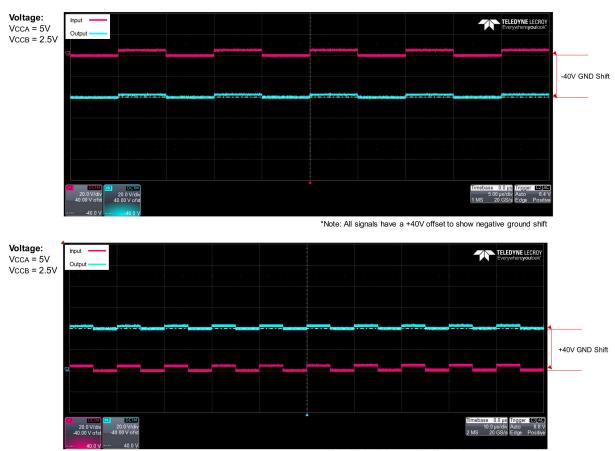
Use the parameters listed in Table 8-1 for this design example.

**Table 8-1. Design Parameters** 

DESIGN PARAMETERS	EXAMPLE VALUES				
Input voltage range	1.71V to 5.5V				
Output voltage range	1.71V to 5.5V				



#### 8.2.2 Application Curve



\*Note: All signals have a -40V offset to show positive ground shift

Figure 8-2. Waveform showing -40V (top) and +40V (bottom) Ground Shift with 2.25V to 5V I/O Translation

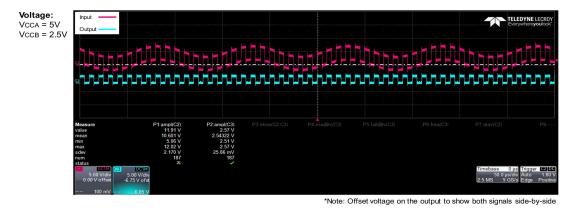


Figure 8-3. Waveform showing 5V to 2.5V I/O Translation with AC Ground Noise of 10kHz at 2VPP



#### 8.3 Power Supply Recommendations

Always apply a ground reference to the GND pins first. This device is designed for glitch free power sequencing without any supply sequencing requirements such as ramp order or ramp rate. Please make sure the difference between VCC and GND remains at 6.5V max at all times.

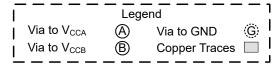
#### 8.4 Layout

#### 8.4.1 Layout Guidelines

To ensure reliability of the device, following common printed-circuit board layout guidelines are recommended:

- Use bypass capacitors on the power supply pins and place them as close to the device as possible. A 0.1μF capacitor is recommended, but transient performance can be improved by having 1μF and 0.1μF capacitors in parallel as bypass capacitors.
- The high drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing.
- A 0.1µF capacitor can be added between GNDA and GNDB to improve performances of CMTI.

#### 8.4.2 Layout Example



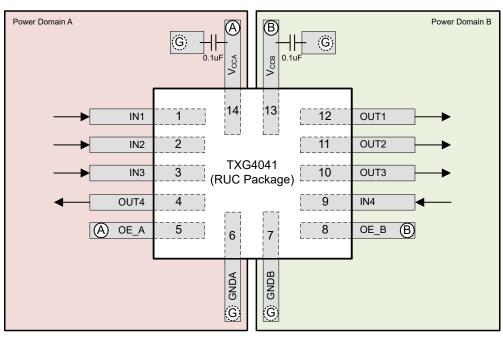


Figure 8-4. Layout Example



## 9 Device and Documentation Support

#### 9.1 Documentation Support

#### 9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, Understanding Schmitt Triggers application report
- Texas Instruments, CMOS Power Consumption and Cpd Calculation application report

## 9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 9.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 9.4 Trademarks

TI E2E<sup>™</sup> is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

#### 9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

## 9.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

#### 10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
February 2025	*	Initial APL Release

## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 21-Feb-2025

#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
PTXG4041QRUCRQ1	ACTIVE	QFN	RUC	14	3000	TBD	Call TI	Call TI	-40 to 125		Samples
PTXG4042QRUCRQ1	ACTIVE	QFN	RUC	14	3000	TBD	Call TI	Call TI	-40 to 125		Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



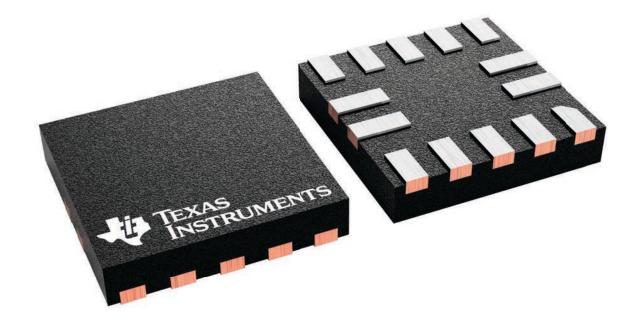
# **PACKAGE OPTION ADDENDUM**

www.ti.com 21-Feb-2025

2 x 2, 0.4 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



#### IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2025. Texas Instruments Incorporated